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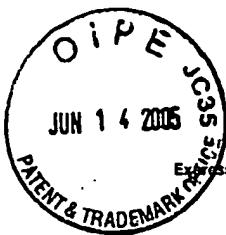
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U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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		Country Code ² -Number ³ -Kind Code ⁴ (if known)	MM-DD-YYYY			

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Examiner Signature	HEN NGUYEN	Date Considered	12/01/05
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PTO/SB/08a/b (08-03)

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Substitute for form 1449A/B/PTO				Complete if Known	
				Application Number	10/796,270-Conf. #2382
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Filing Date	March 9, 2004
				First Named Inventor	Jack Z. Peng
				Art Unit	2824
				Examiner Name	H. N. Nguyen
				Attorney Docket Number	384848010US
Sheet	2	of	2		

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²

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¹Applicant's unique citation designation number (optional). ²Applicant is to place a check mark here if English language Translation is attached.

Examiner Signature	H. N. Nguyen	Date Considered	12/01/05
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT Form PTO-1449 (Modified) (Use several sheets if necessary)				COMPLETE IF KNOWN	
				Application Number	10/796,270
				Confirmation Number	
				Filing Date	
				First Named Inventor	Jianguo Wang
				Group Art Unit	H. NGUYEN 2824
Examiner Name					
Sheet	1	of	4	Attorney Docket No.	384848010US

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				Group Art Unit	2824
Examiner Name	H. NGUYEN				
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				Filing Date	
				First Named Inventor	Jianguo Wang
				Group Art Unit	2824
Examiner Name	H. Nguyen				
Sheet	3	of	4	Attorney Docket No.	384848010US

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